



No.4423A

3SK263

N-Channel MOS Silicon FET (Dual Gate)

FM Tuner, VHF Tuner,
High-Frequency Amp Applications

Features

- Enhancement type.
- Small noise figure.
- Small cross modulation.

Absolute Maximum Ratings at Ta = 25°C

			unit
Drain-to-Source Voltage	V _{DS}	15	V
Gate1-to-Source Voltage	V _{G1S}	±8	V
Gate2-to-Source Voltage	V _{G2S}	±8	V
Drain Current	I _D	30	mA
Allowable Power Dissipation	P _D	200	mW
Channel Temperature	T _{ch}	125	°C
Storage Temperature	T _{stg}	-55 to +125	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Drain-to-Source Voltage	V _{DS}	V _{G1S} =0V, V _{G2S} =0V, I _D =100μA	15			V
Gate1-to-Source Cutoff Voltage	V _{G1S(off)}	V _{DS} =6V, V _{G2S} =4V, I _D =100μA	0	0.7	1.3	V
Gate2-to-Source Cutoff Voltage	V _{G2S(off)}	V _{DS} =6V, V _{G1S} =3V, I _D =100μA	0.1	0.9	1.6	V
Gate1 Cutoff Current	I _{G1SS}	V _{G1S} =±6V, V _{G2S} =V _{DS} =0V			±50	nA
Gate2 Cutoff Current	I _{G2SS}	V _{G2S} =±6V, V _{G1S} =V _{DS} =0V			±50	nA
Drain Current	I _{DSX}	V _{DS} =6V, V _{G1S} =1.5V, V _{G2S} =4V	2.5*		24*	mA
Forward Transfer Admittance	Y _{fs}	V _{DS} =6V, I _D =10mA, V _{G2S} =4V, f=1kHz		14		mS
Input Capacitance	C _{iss}	V _{DS} =6V, f=1MHz		2.7		pF
Reverse Transfer Capacitance	C _{rss}	V _{G1S} =0V, V _{G2S} =4V		0.015	0.03	pF
Power Gain	PG	V _{DS} =6V, I _D =10mA	18	21		dB
Noise Figure	NF	V _{G2S} =4V, f=200MHz		1.1	2.2	dB

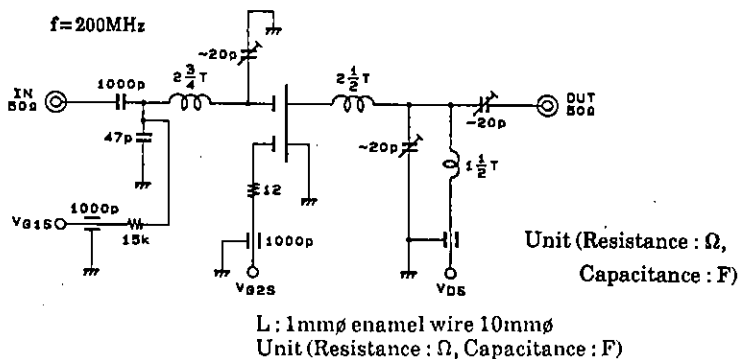
* : The 3SK263 is classified by I_{DSX} as follows : (unit : mA)

2.5	4	6.0	5.0	5	12.0	10.0	6	24.0
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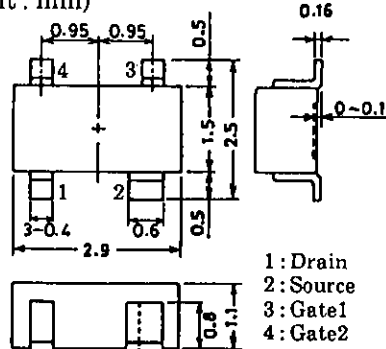
Marking : RJ

I_{DSX} rank : 4, 5, 6

PG, NF Test Circuit

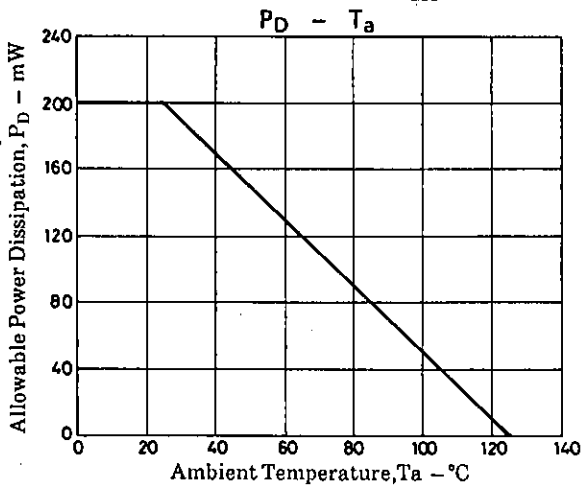
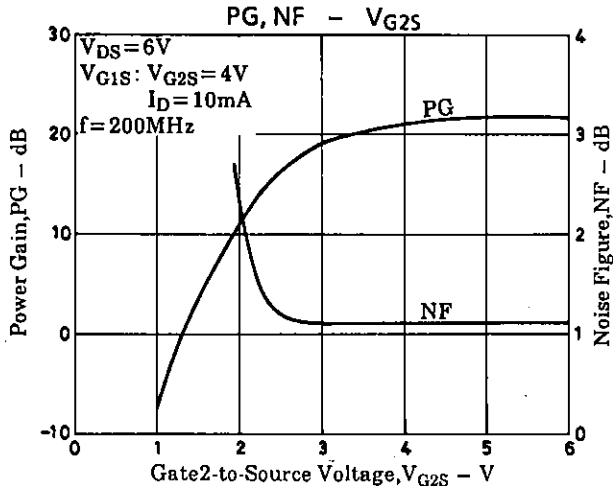
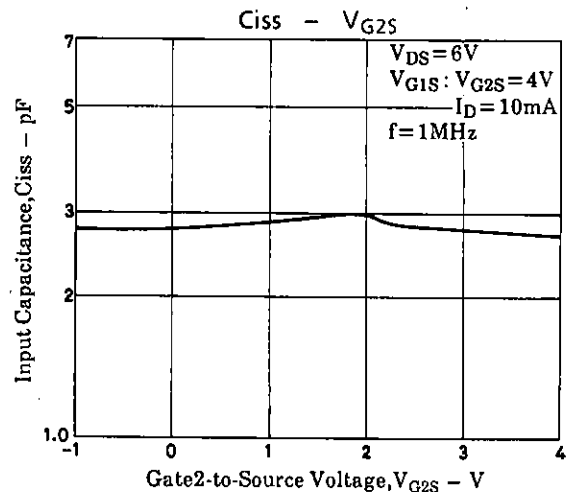
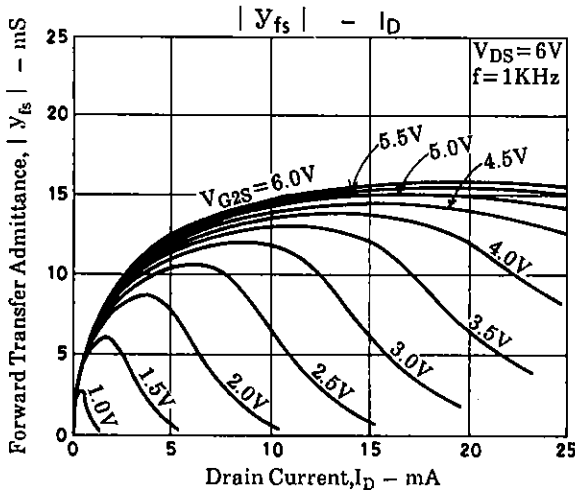
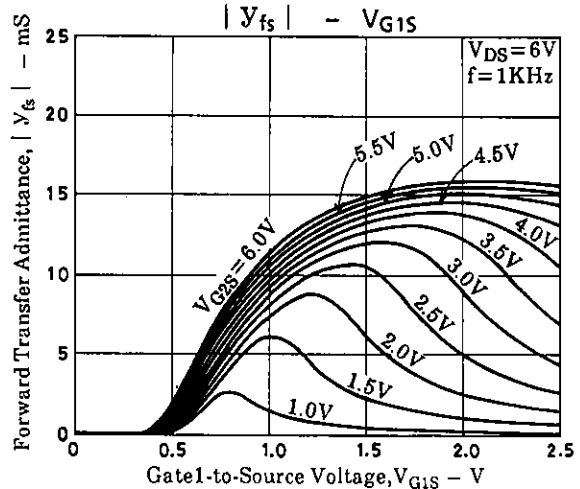
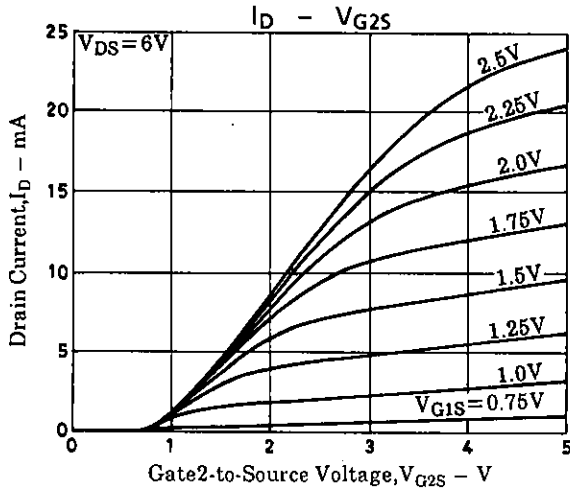
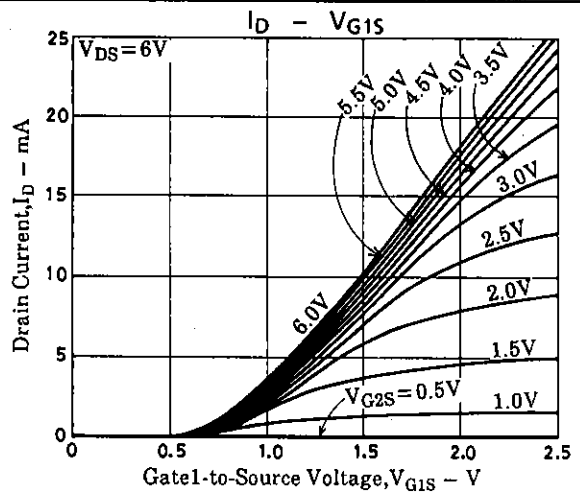
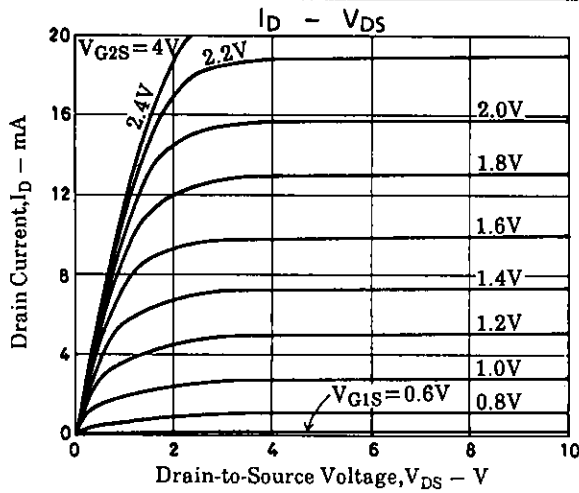


Package Dimensions 2096A
(unit : mm)



SANYO : CP4

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